

N-channel 80 V, 4.5 mΩ standard level MOSFET in D2PAK

Rev. 1 — 22 March 2012

Product data sheet

1. Product profile

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1.1 General description

Standard level N-channel MOSFET in SOT404 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	80	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	306	W
Tj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see <u>Figure 13</u> ; see <u>Figure 6</u>		-	6.27	7.4	mΩ
		$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \; V; \; I_D = 25 \; A; \; T_j = 25 \; ^\circ C; \\ \text{see} \; \underline{Figure \; 6} \end{array}$		-	3.8	4.5	mΩ
Dynamic	characteristics						
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I_{D} = 25 A; V_{DS} = 40 V;		-	25	-	nC
Q _{G(tot)}	total gate charge	see Figure 14; see Figure 15		-	125	-	nC
	e ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C};$ $I_D = 100 \text{ A}; \text{ V}_{sup} \le 80 \text{ V};$ $R_{GS} = 50 \Omega;$ unclamped		-	-	591	mJ

[1] Continuous current is limited by package

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain ^[1]	mb	
3	S	source		
mb	D	drain	ii	
				mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2

3. Ordering information

Table 3. Ordering information Type number Package Name Description Version PSMN4R4-80BS D2PAK plastic single-ended surface-mounted package (D2PAK); 3 leads SOT404 (one lead cropped)

4. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN4R4-80BS	PSMN4R4-80BS

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		J				
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	80	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	80	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; see <u>Figure 3</u>		-	680	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	306	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-dra	ain diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	680	А
Avalanche	ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V}; T_{j(init)} = 25 ^{\circ}\text{C}; \text{I}_{\text{D}} = 100 \text{ A}; \\ V_{sup} \leq 80 \text{ V}; \text{R}_{GS} = 50 \Omega; \text{ unclamped} \end{array} $		-	591	mJ
-						

[1] Continuous current is limited by package

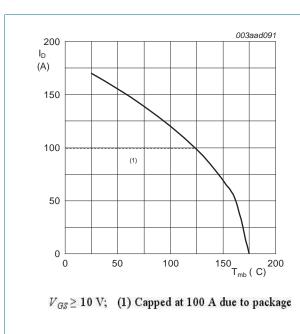
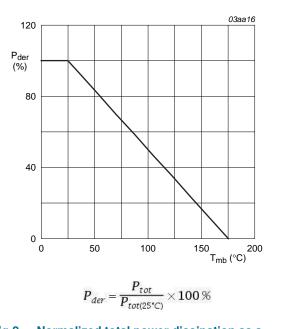


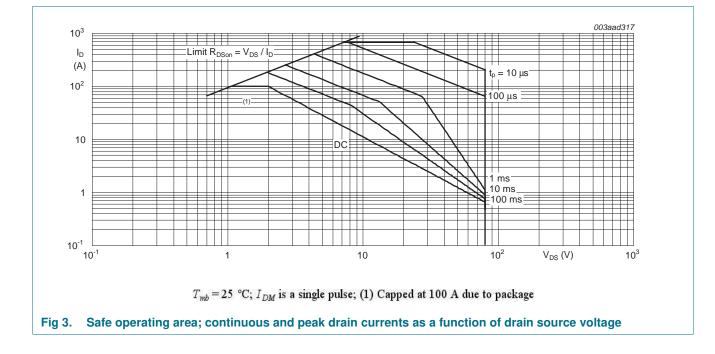
Fig 1. Normalized continuous drain current as a function of mounting base temperature





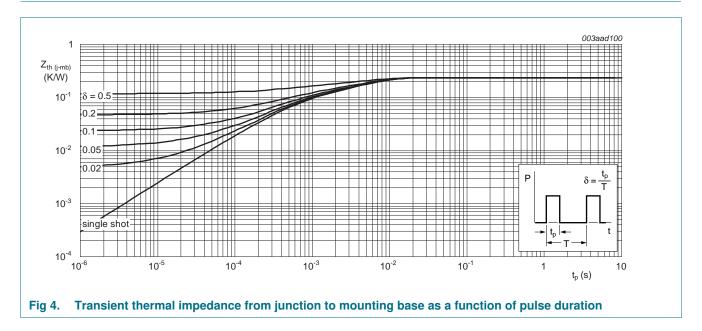
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6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.23	0.49	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W



7. Characteristics

Table 7. Characteristics

Tested to JEDEC standards where applicable.

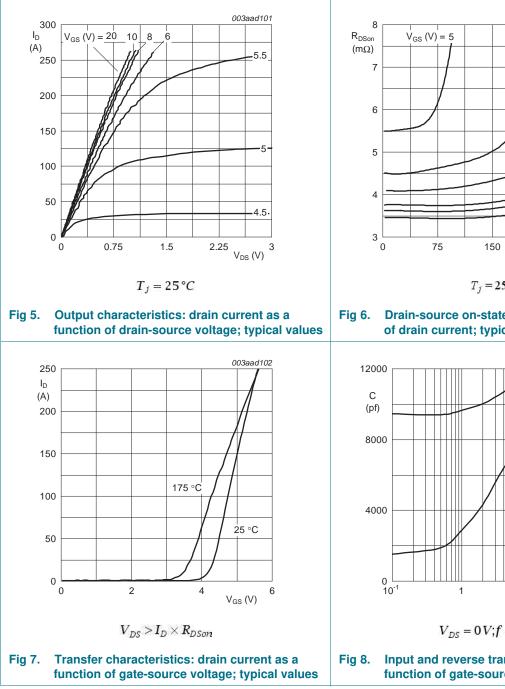
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	73	-	-	V
		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	80	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 11</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 11	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	10	μA
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	200	μA
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R _{DSon} drain-source on-state resistance	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see <u>Figure 13</u> ; see <u>Figure 6</u>	-	9.12	10.7	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see <u>Figure 13</u> ; see <u>Figure 6</u>	-	6.27	7.4	mΩ
	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 6</u>	-	3.8	4.5	mΩ	
R _G	internal gate resistance (AC)	f = 1 MHz	-	1	-	Ω
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	112	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	125	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	39	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	24	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	15	-	nC
Q _{GD}	gate-drain charge		-	25	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15};$ see $\frac{\text{Figure } 15}{\text{Figure } 15}$	-	4.65	-	V
C _{iss}	input capacitance	$V_{DS} = 40 V; V_{GS} = 0 V; f = 1 MHz;$	-	8400	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 16$	-	700	-	pF
C _{rss}	reverse transfer capacitance		-	336	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 40 \text{ V}; \text{ R}_{L} = 0.5 \ \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	34.7	-	ns
t _r	rise time	$R_{G(ext)} = 1.5 \Omega$	-	38.1	-	ns
t _{d(off)}	turn-off delay time		-	66	-	ns
t _f	fall time		-	18.4	-	ns

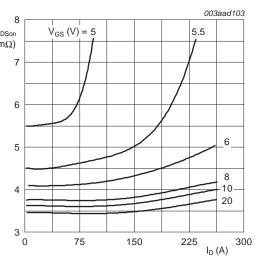
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Table 7. Characteristics ... continued

Tested to JEDEC standards where applicable.

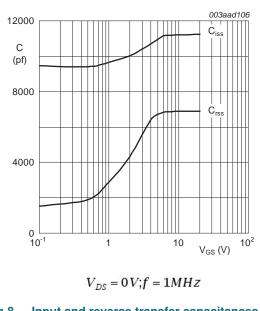
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	ain diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = 100 \text{ A}/\mu\text{s};$	-	59	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 20 V$	-	130	-	nC









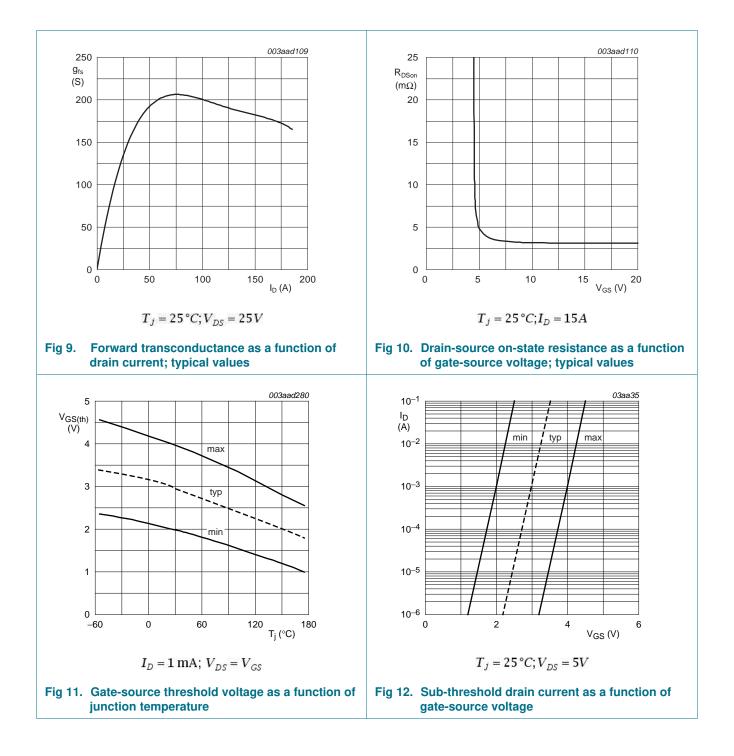




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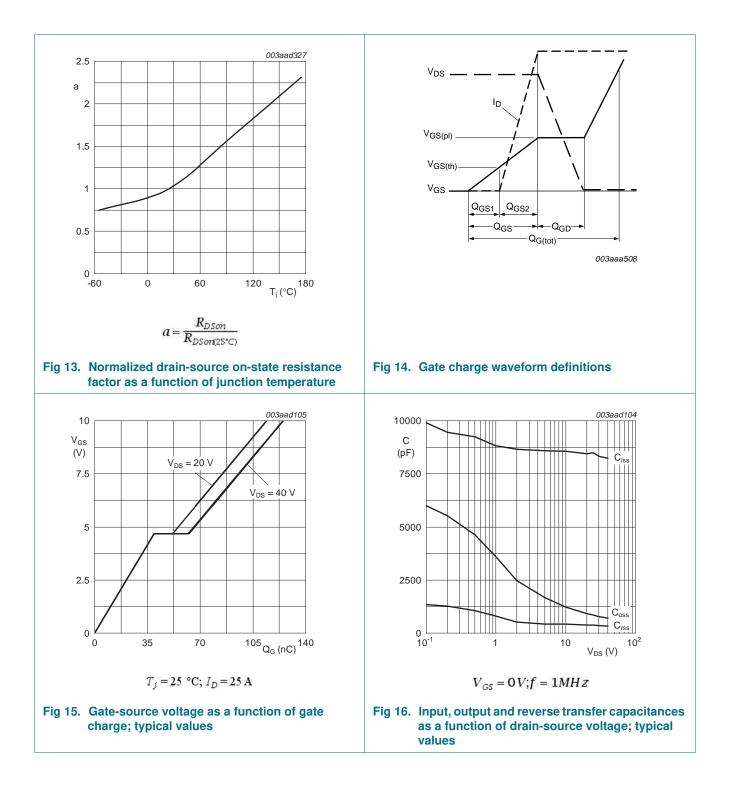
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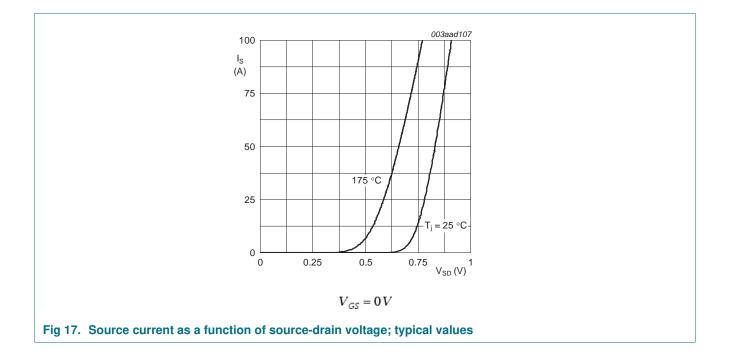
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8. Package outline

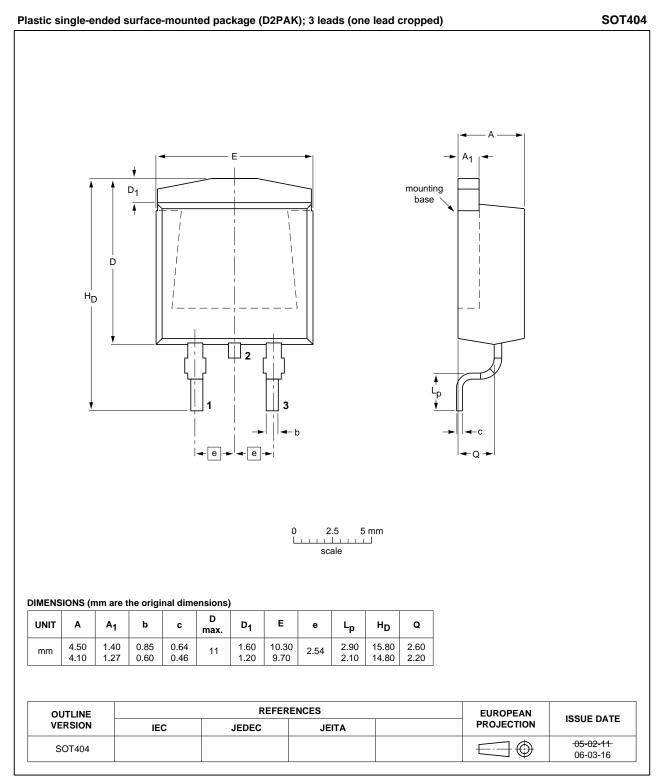


Fig 18. Package outline SOT404 (D2PAK)

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9. Revision history

Table 8. Revision	Revision history							
Document ID	Release date	Data sheet status	Change notice	Supersedes				
PSMN4R4-80BS v.1	20120322	Product data sheet	-	-				

10. Legal information

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Document status ^[1] ^[2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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